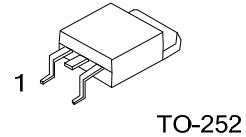
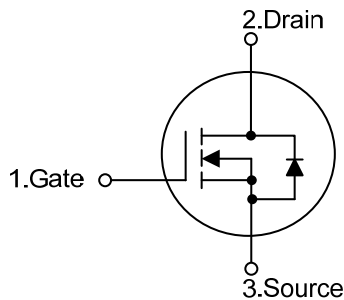


**F11NM90-Q****Power MOSFET****11A, 900V N-CHANNEL
SUPER-JUNCTION MOSFET****DESCRIPTION**

The **UTC F11NM90-Q** is a Super Junction MOSFET Structure and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and a high rugged avalanche characteristics. This power MOSFET is usually used at AC-DC converters for power applications.

FEATURES

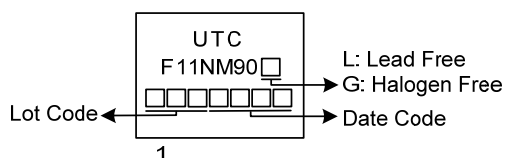
- * $R_{DS(ON)} \leq 0.92 \Omega$ @ $V_{GS}=10V$, $I_D=5.5A$
- * Fast switching capability
- * Avalanche energy tested
- * Improved dv/dt capability, high ruggedness

SYMBOL**ORDERING INFORMATION**

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
F11NM90L-TN3-R	F11NM90G-TN3-R	TO-252	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

	(1) Packing Type	(1) R: Tape Reel
	(2) Package Type	(2) TN3: TO-252
	(3) Green Package	(3) G: Halogen Free and Lead Free, L: Lead Free

MARKING

■ ABSOLUTE MAXIMUM RATINGS (T_C=25°C, unless otherwise specified)

PARAMETER			SYMBOL	RATINGS	UNIT
Drain-Source Voltage			V _{DSS}	900	V
Gate-Source Voltage			V _{GSS}	±30	V
Drain Current	Continuous	T _C =25°C	I _D	11	A
		T _C =100°C		7.1	A
	Pulsed (Note 2)		I _{DM}	33	A
Avalanche Energy	Single Pulsed (Note 3)		E _{AS}	162	mJ
Peak Diode Recovery dv/dt (Note 4)			dv/dt	1.5	V/ns
Power Dissipation			P _D	36	W
Junction Temperature			T _J	+150	°C
Storage Temperature			T _{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
 2. Repetitive Rating: Pulse width limited by maximum junction temperature.
 3. L = 100mH, I_{AS} = 1.8A, V_{DD} = 90V, R_G = 25Ω, Starting T_J = 25°C
 4. I_{SD} ≤ 11A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C

■ THERMAL DATA

PARAMETER	SYMBOL	RATING	UNIT
Junction to Ambient	θ _{JA}	110	°C/W
Junction to Case	θ _{JC}	3.47	°C/W

Note: Device mounted on FR-4 substrate P_c board, 2oz copper, with 1inch square copper plate.

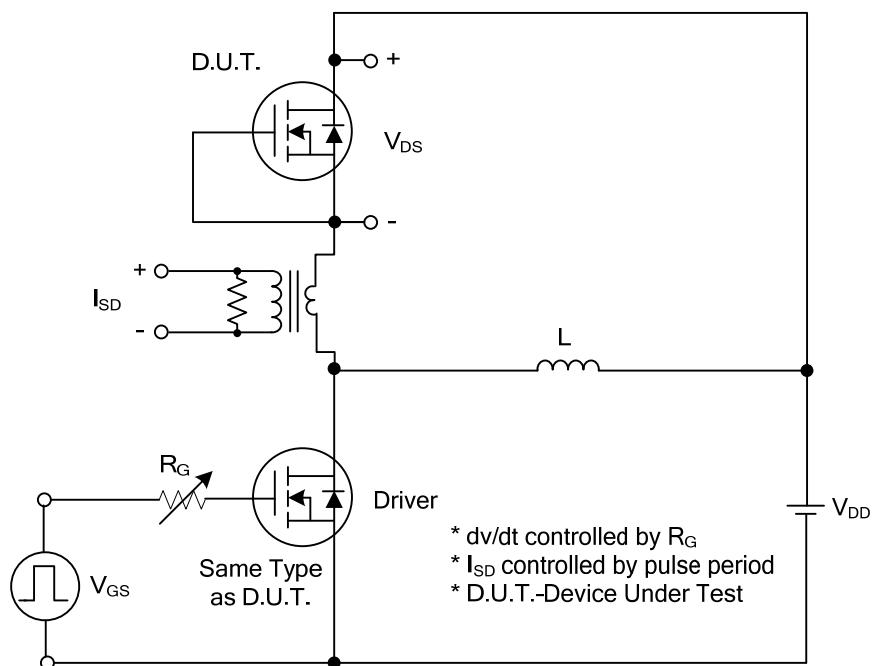
■ **ELECTRICAL CHARACTERISTICS** ($T_J=25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	900			V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =900V, V _{GS} =0V			10	μA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±30V, V _{DS} =0V			±100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _D =250μA	2.5		4.5	V
Static Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =5.5A			0.92	Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{ISS}	V _{GS} =0V, V _{DS} =50V, f=1MHz		700		pF
Output Capacitance	C _{OSS}			116		pF
Reverse Transfer Capacitance	C _{RSS}			5.3		pF
SWITCHING CHARACTERISTICS						
Total Gate Charge	Q _G	V _{DS} =720V, V _{GS} =10V, I _D =11A (Note 1, 2)		43.8		nC
Gate-Source Charge	Q _{GS}			15		nC
Gate-Drain Charge	Q _{DD}			15.4		nC
Turn-On Delay Time	t _{D(ON)}	V _{DD} =100V, V _{GS} =10V, I _D =11A, R _G =25Ω (Note 1, 2)		12		ns
Turn-On Rise Time	t _{tr}			24		ns
Turn-Off Delay Time	t _{D(OFF)}			90		ns
Turn-Off Fall Time	t _f			42		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Continuous Drain-Source Diode Forward Current	I _S				11	A
Maximum Pulsed Drain-Source Diode Forward Current	I _{SM}				33	A
Drain-Source Diode Forward Voltage	V _{SD}	I _S =11A, V _{GS} =0V			1.4	V
Body Diode Reverse Recovery Time	t _{rr}	I _S =11A, V _{GS} =0V,		220		nS
Body Diode Reverse Recovery Charge	Q _{rr}	dl _F /dt=100A/μs		1.8		μC

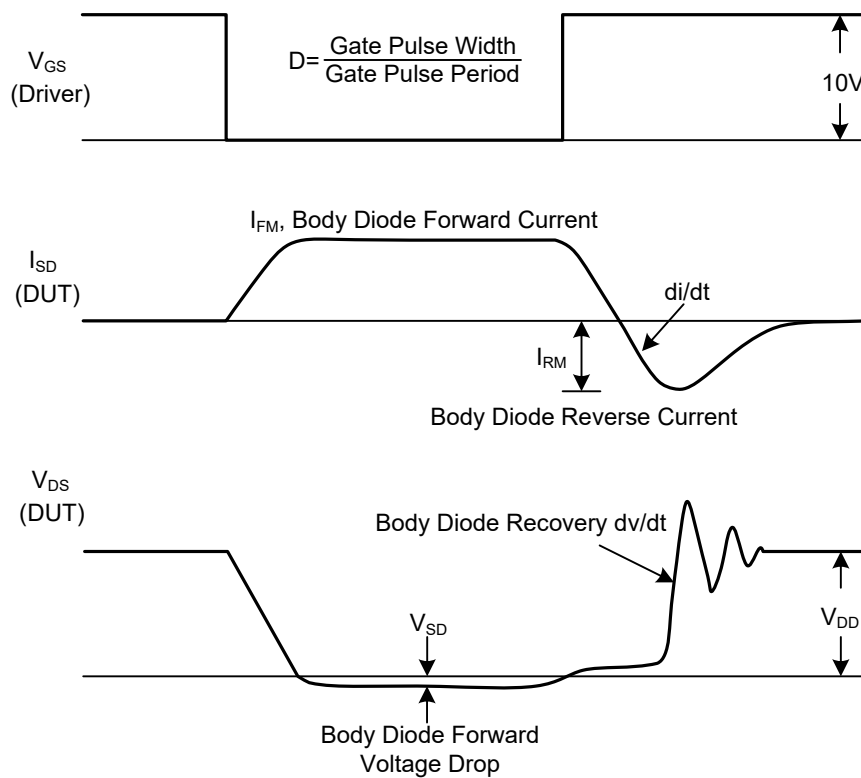
Notes: 1. Pulse Test: Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

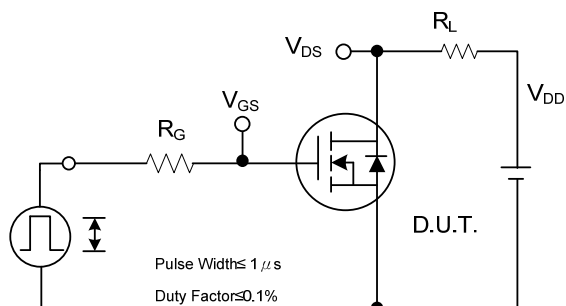


Peak Diode Recovery dv/dt Test Circuit

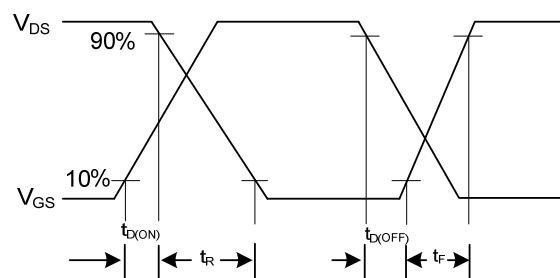


Peak Diode Recovery dv/dt Waveforms

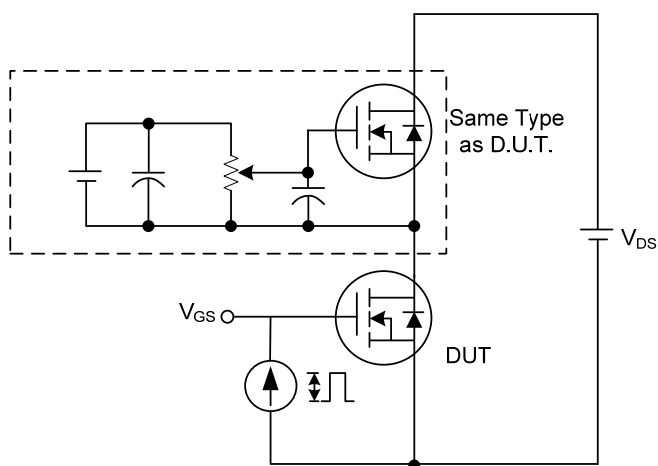
■ TEST CIRCUITS AND WAVEFORMS



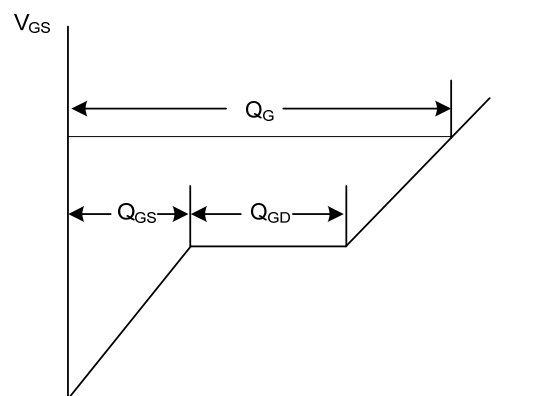
Switching Test Circuit



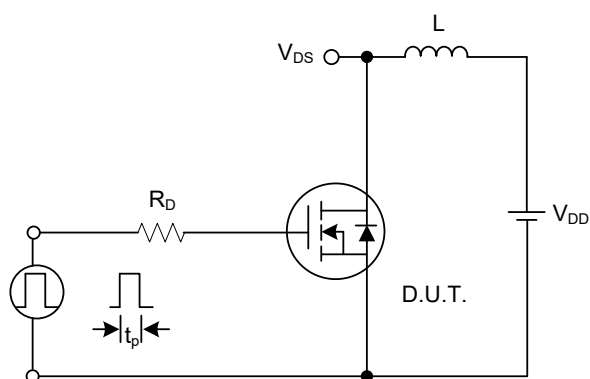
Switching Waveforms



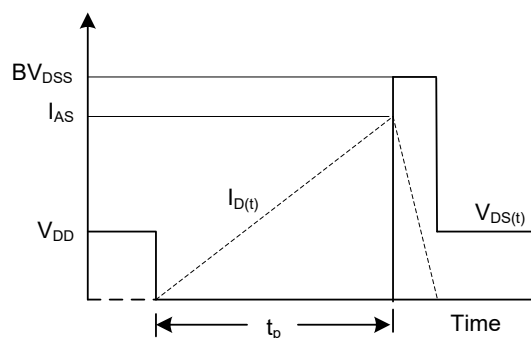
Gate Charge Test Circuit



Charge
Gate Charge Waveform

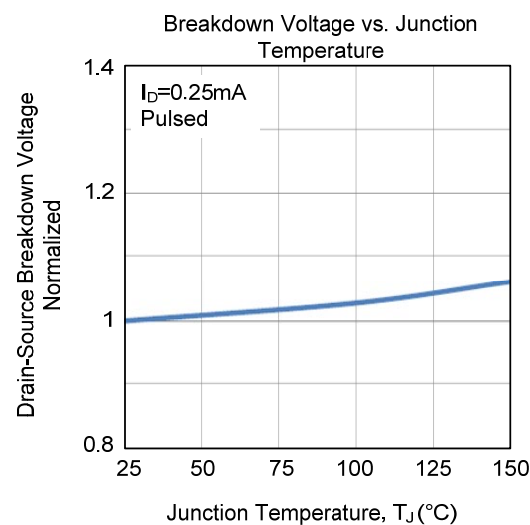
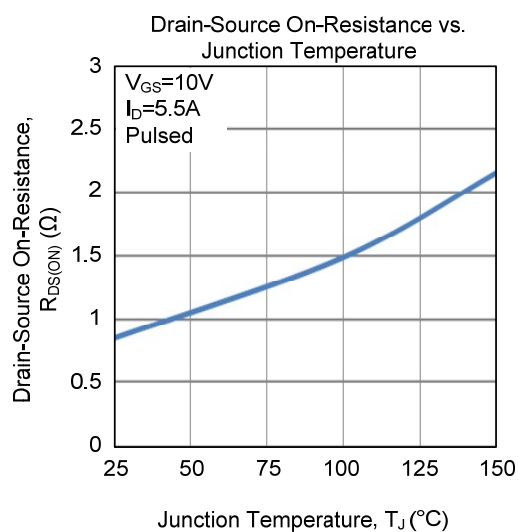
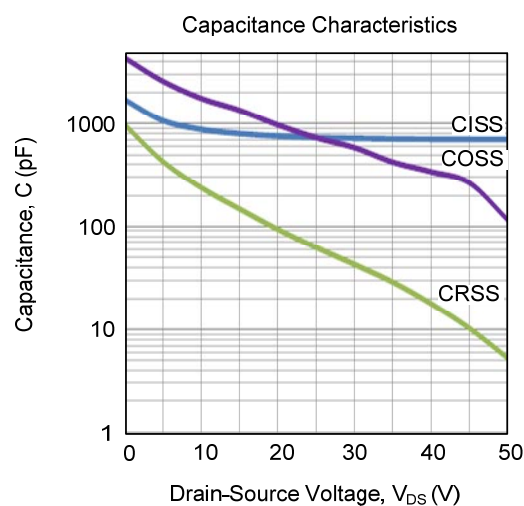
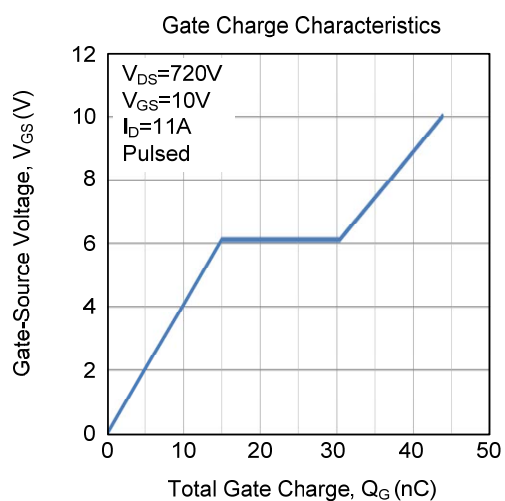
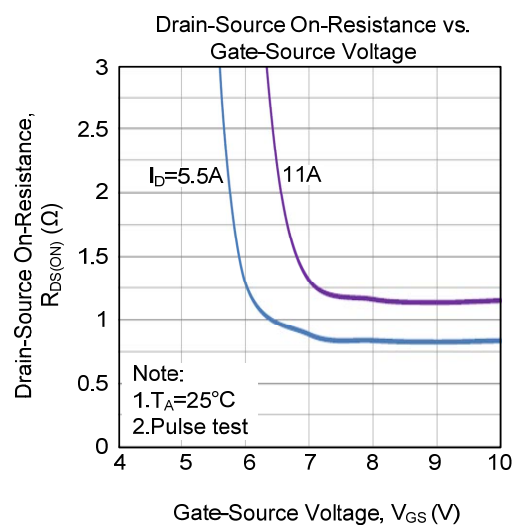
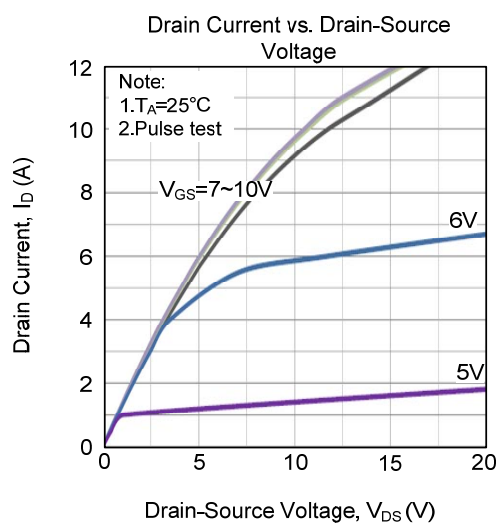


Unclamped Inductive Switching Test Circuit

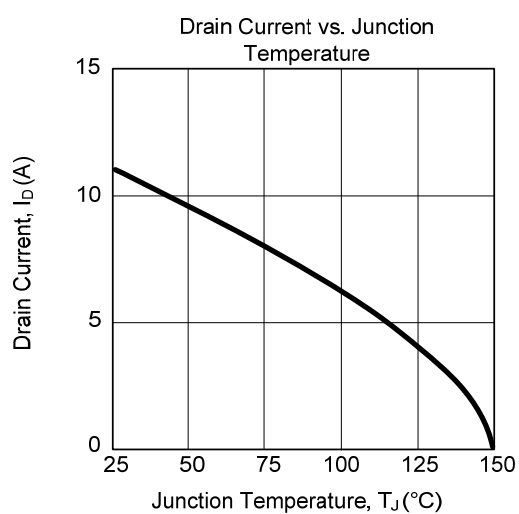
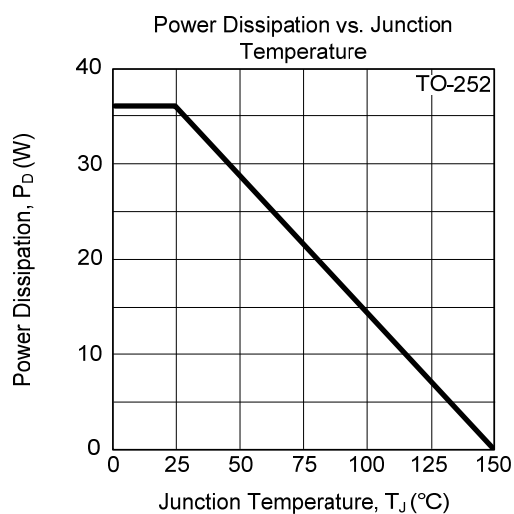
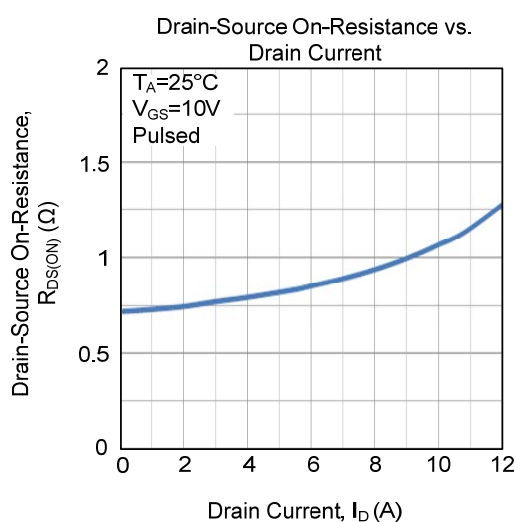
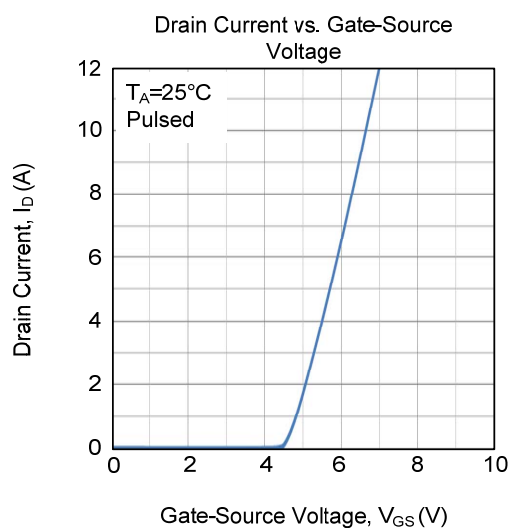
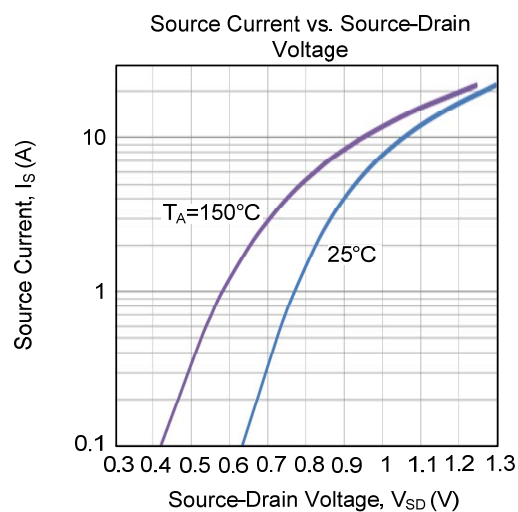
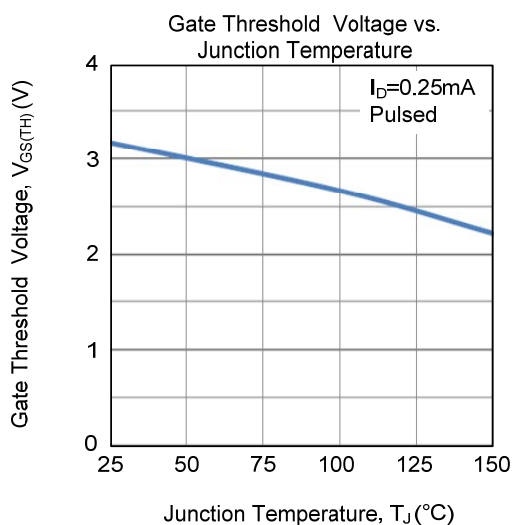


Unclamped Inductive Switching Waveforms

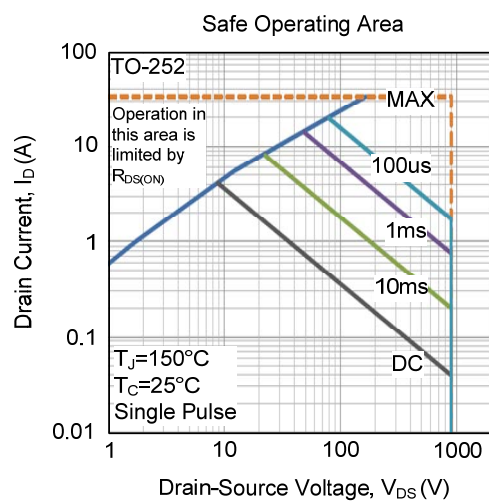
TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS (Cont.)



■ TYPICAL CHARACTERISTICS (Cont.)



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